

150V PNP HIGH VOLTAGE TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistor (BJT) has been designed to meet the stringent requirements of automotive applications.

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type MMBT5551Q
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMBT5401Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

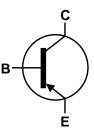
https://www.diodes.com/quality/product-definitions/

Mechanical Data

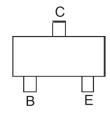
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208³
- Weight: 0.008 grams (Approximate)







Device Symbol



Top View Pin-Out

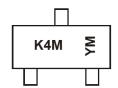
Ordering Information (Note 4)

Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
Fait Number	Fackage	wai kiliy	Reel Size (Illulies)	rape widin (iiiii)	Qty.	Carrier
MMBT5401Q-7-F	SOT23	K4M	7	8	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: L = 2024) M = Month (ex: 3 = March)

Date Code Key

Year	2017	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	Е	-	L	М	N	Р	R	S	Т	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	Ic	-600	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D-	310	mW
Power Dissipation	(Note 6)	P _D	350	IIIVV
Thermal Resistance, Junction to Ambient	(Note 5)	D	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	357	C/VV
Thermal Resistance, Junction to Leads (Note 7)		Rejl	350	°C/W
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

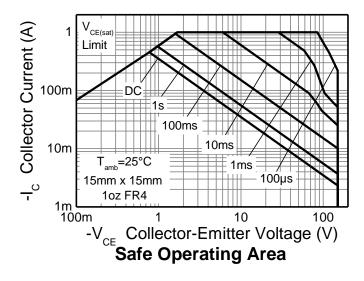
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

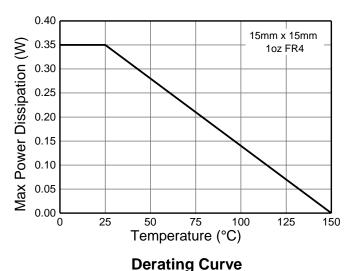
Notes:

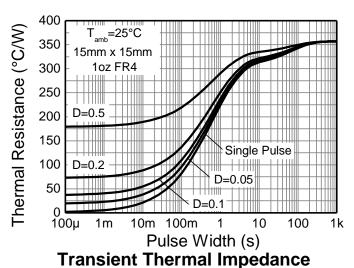
- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air For a device mounted of minimum recommended pad layout 102 copper that is conditions whilst operating in a steady-state.
 Same as note (5), except the device is mounted on 15mm x 15mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the leads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.

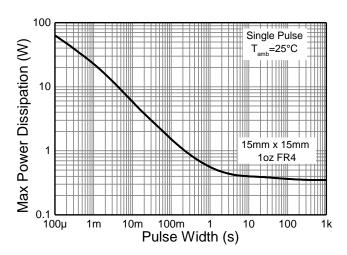


Thermal Characteristics and Derating Information









Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)					
Collector-Base Breakdown Voltage	ВУсво	-160	_	V	$I_C = -100\mu A$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BVceo	-150	_	V	$I_{C} = -1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	Ісво	_	-50	nA	V _{CB} = -120V, I _E = 0
00.0000.000.0000	1000		-50	μA	$V_{CB} = -120V$, $I_{E} = 0$, $T_{A} = +100^{\circ}C$
Emitter Cutoff Current	IEBO	_	-50	nA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)					
		50	_		Ic = -1mA, $VcE = -5V$
DC Current Gain	h _{FE}	60	240	_	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
		50	_		Ic = -50mA, $VcE = -5V$
Collector-Emitter Saturation Voltage	\/a=()		-0.2	V	$I_C = -10mA$, $I_B = -1mA$
Collector-Efficier Saturation Voltage	VCE(sat)		-0.5	V	$I_C = -50 \text{mA}$, $I_B = -5 \text{mA}$
Base-Emitter Saturation Voltage	Vp=()		-1	V	$I_C = -10mA$, $I_B = -1mA$
ŭ	V _{BE} (sat)		- 1	V	$I_C = -50 \text{mA}$, $I_B = -5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	_	6	pF	$V_{CB} = -10V$, $f = 1MHz$, $I_E = 0$
Small Signal Current Gain	h _{fe}	40	260	_	$V_{CE} = -10V$, $I_{C} = -1mA$,
Official Current Curr	1116	10	200		f = 1kHz
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = -10V$, $I_{C} = -10mA$,
	- 1	. 30			f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5V$, $I_{C} = -200\mu A$,
					$R_S = 10\Omega$, $f = 1kHz$

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

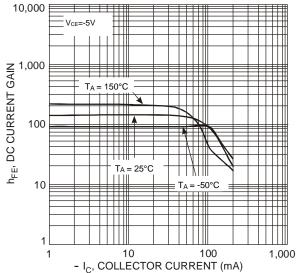
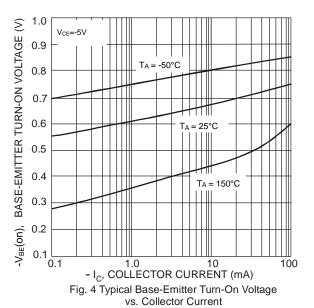


Fig. 2 Typical DC Current Gain vs. Collector Current



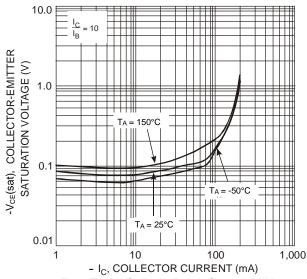


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

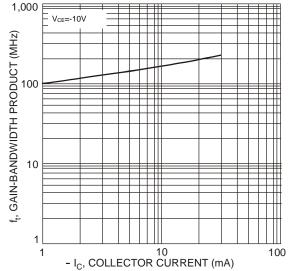


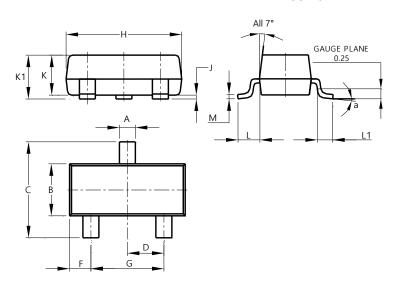
Fig. 5 Typical Gain-Bandwidth Product vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

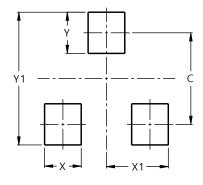


	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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